YJ Planar Schottky Barrier Diode Die Specification

200V 20A, 102mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB102H200AS-280A

Main Products Characterstics

Maximum Ratings

current (tp = 8.3 ms, halfwave, 1 cycle)	I_{FSM}	150 A

Static Electrical Characteristics (Ta = 25°C)

		Value	
		Spec	Typical
		210 V	230V
Maximum forward voltage drop I_F = 20 A	V_F	0.92V	0.88V
≤ 2%			

Maximum operating junction Mdone i3(i)7yBTM43.6*98 Mil2x-183469.63 126.22.17 1T8.8.61 Tm -0.00336 17593uAng (°)350(0.3uAone)>BDC BTF3 8

Device Schematics and Outline Drawing

Die Thickness *	11 Mils
Die Size **	
Top Metal Pad	2*48.6*98 Mils
Active Area	2*43.8*93.4 Mils
Space between die	0.98 Mils
Top Metal	AL
Back Metal	Ag

Note: 1 * : Also can offer device with 8 mils thickness
2 **: Cutting street width is around 1.5 mils

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

does not guarantee device performance after assembly.
All operating parameters must be validated for each customer application by customer's technical experts.

Data sheet information is subjected to change without notice.

Recommended Storage Environment:

Store in original container, in dessicated nitrogen, with no contamination.

Shelf life for parts stored in above condition is 2 years.

If the storage is done in normal atmosphere shelf life is reduced to 6 months.

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